

L Number	Hits	Search Text	DB	Time stamp
1	2	("6121121").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 10:46
2	30	6121121.URPN.	USPAT	2004/01/22 10:16
3	13	("5185290" "5239188" "5798536" "6051849" "6110277" "6121121" "6146457" "6153010" "6274518" "6319742" "6329667" "6355497" "6365921").PN.	USPAT	2004/01/22 10:24
4	18	("Re34861" "4127792" "4522661" "4651407" "4865685" "4876210" "4912064" "4946547" "5122845" "5389571" "5397736" "5549747" "5710057" "5760426" "5786606" "5815520" "5877070" "5880485").PN.	USPAT	2004/01/22 10:28
5	29	("4127792" "4522661" "4651407" "4865685" "4876210" "4912064" "4946547" "5122845" "5156995" "RE34861" "5389571" "5397736" "5549747" "5710057" "5760426" "5786606" "5815520" "5877070" "5880485" "5912477" "5915194" "6051849" "6064078" "6100104" "6100111" "6121121" "6153010" "6156584" "6325850").PN.	USPAT	2004/01/22 10:35
6	7	("5880485" "5953581" "6015979" "6111277" "6121121" "6225650" "6316785").PN.	USPAT	2004/01/22 10:40
7	3	("5727008" "6015979" "6153010").PN.	USPAT	2004/01/22 10:40
8	10669	257/13,79-103,918;438/22,24,25,28,29,46,47.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 10:52
9	5332	257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:35
10	5	(257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and (GaN NEAR III NEAR V NEAR group)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 10:54
11	1226	(257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:36
12	1182	((257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:08
13	7	("5880485" "5953581" "6015979" "6111277" "6121121" "6225650" "6316785").PN.	USPAT	2004/01/22 11:03
14	3	("5727008" "6015979" "6153010").PN.	USPAT	2004/01/22 11:04
15	2	((257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and substrate) and (isolat\$3 NEAR block\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:09
16	146	((257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and substrate) and (oxid\$4 NEAR layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:10

17	102	(((257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and substrate) and (oxid\$4 NEAR layer)) and (active NEAR layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:11
18	0	(257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and (lateral NEAR growth NEAR technology)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:48
19	334971	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:44
20	2	(257/\$.ccls. 438/\$.ccls.) and (lateral NEAR growth NEAR technology)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:47
21	13	("3697829" "4211586" "4242690" "4375125" "4642669" "4667393" "4927772" "4947218" "5119148" "5449925" "5459089" "5650638" "5814840").PN.	USPAT	2004/01/22 11:45
22	8	("3697829" "4211586" "4375125" "4642669" "4667393" "4927772" "5449925" "5459089").PN.	USPAT	2004/01/22 11:46
23	419719	((light NEAR emit\$4 NEAR diode) LED)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:47
24	0	(((light NEAR emit\$4 NEAR diode) LED)) and (lateral NEAR growth NEAR technology)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:47
25	4	lateral NEAR growth NEAR technology	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:47
26	96	(257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and (lateral NEAR grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:51
27	0	((257/13,79-103,918;438/22,24,25,28,29,46,47.ccls. and ((light NEAR emit\$4 NEAR diode) LED)) and (lateral NEAR grow\$3)) and ((mix\$3 NEAR ratio) WITH (grow\$3 NEAR gas) WITH (etch\$3 NEAR gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:50
28	1233	(257/\$.ccls. 438/\$.ccls.) and (lateral NEAR grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:00
29	0	((257/\$.ccls. 438/\$.ccls.) and (lateral NEAR grow\$3)) and ((mix\$3 NEAR ratio) WITH (grow\$3 NEAR gas) WITH (etch\$3 NEAR gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 11:50

30	0	((mix\$3 NEAR ratio) WITH (grow\$3 NEAR gas) WITH (etch\$3 NEAR gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:00
31	0	(mix\$3 NEAR ratio) and ((grow\$3 NEAR gas) WITH (etch\$3 NEAR gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:00
32	60513	(mix\$3 NEAR ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:00
33	43	((mix\$3 NEAR ratio)) and (lateral NEAR grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:35
34	2178	lateral NEAR grow\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:35
35	342	(lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:50
36	208	((lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)) and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:59
37	179	((lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and (buffer NEAR (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:00
38	6	((lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)) and GaN) and ((buffer NEAR (layer film)) WITH oxid\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:46
39	36	((lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)) and (GaN NEAR epi\$6 NEAR layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 12:59
40	31	((lateral NEAR grow\$3) and ((light NEAR emit\$4 NEAR diode) LED)) and (GaN NEAR epi\$6 NEAR layer)) and (buffer NEAR (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:00
41	0	(buffer NEAR (layer film) NEAR GaN) WITH (oxid\$5 NEAR layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:47

42	5	(buffer NEAR (layer film) NEAR GaN) WITH oxid\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:50
43	1078	(buffer NEAR (layer film) NEAR GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:50
44	639	((buffer NEAR (layer film) NEAR GaN)) and ((light NEAR emit\$4 NEAR diode) LED)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:50
45	78	((((buffer NEAR (layer film) NEAR GaN)) and ((light NEAR emit\$4 NEAR diode) LED)) and (lateral NEAR grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/22 13:51